

No.2407

DSC30T

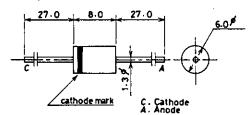
Diffused Junction Type Silicon Diode 3.0A Power Rectifier

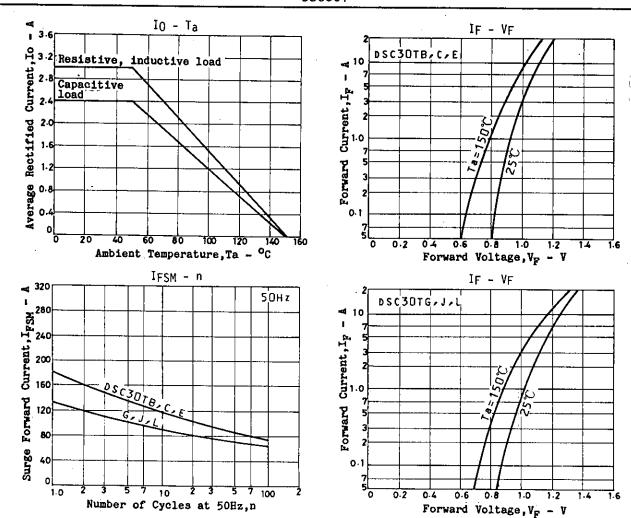
Features

- . Peak reverse voltage $\rm V_{RM}\text{=-}100$ to --1000V . Average rectified current Io=3.0A

Absolute Maximum Ratings at Peak Reverse Voltage Average Rectified Current Surge Forward Current Junction Temperature Storage Temperature	V _{PM}	6C30TB -100 → ->	$\overset{\longrightarrow}{\rightarrow}$	-400 3.0	V
Peak Reverse Voltage Average Rectified Current Surge Forward Current Junction Temperature Storage Temperature	$V_{\rm RM}$ Io Ta=50°C $I_{\rm FSM}$ 50Hz sine wave, 1 cycle Tj Tstg	-600 -600 → → →	\rightarrow	-1000 3.0	unit V A A OC OC
Electrical Characteristics a Forward Voltage V_F Reverse Current I_R	at Ta=25°C I _F =3.0A(B,C,E) I _F =3.0A(G,J,L) V _R : At each V _{RM}	min	1	nax unit .0 V .1 V .10 uA	-

Package Dimensions 1176 (unit: mm)





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